

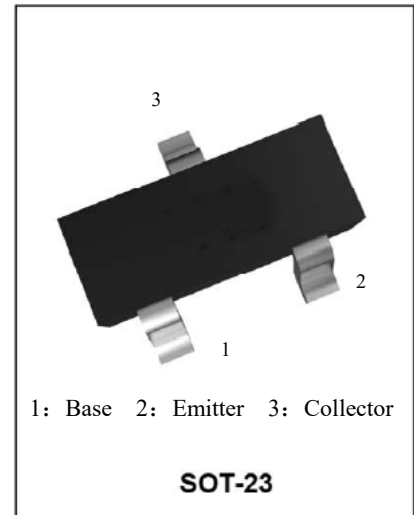
## Silicon Epitaxial Planar Transistor

### FEATURES

- High Collector Current.(Ic= -500mA)
- Complementary To S8050.
- Excellent H<sub>FE</sub> Linearity.

### APPLICATIONS

- High Collector Current.



### ORDERING INFORMATION

Type No.	Marking	Package Code
S8550	2TY	SOT-23

### MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units
V <sub>CB0</sub>	Collector-Base Voltage	-40	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-25	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current -Continuous	-500	mA
P <sub>C</sub>	Collector Dissipation	300	mW
T <sub>j</sub> , T <sub>stg</sub>	Junction and Storage Temperature	-55~150	°C

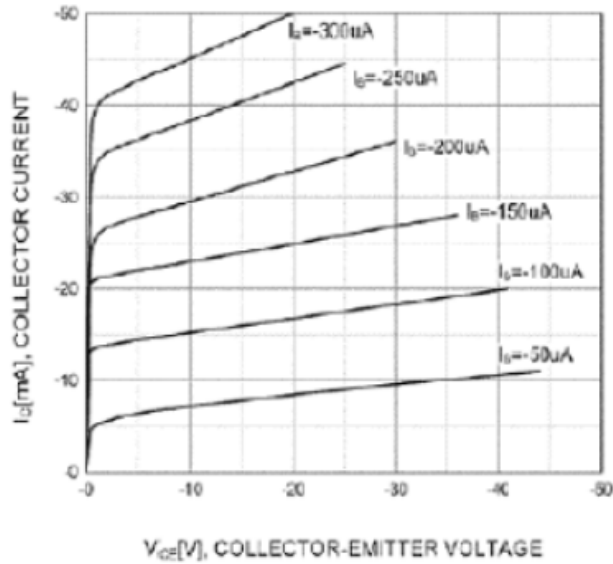
**ELECTRICAL CHARACTERISTICS** @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5		V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -40V, I_E = 0$		-0.1	$\mu A$
Collector cut-off current	$I_{CEO}$	$V_{CE} = -20V, I_B = 0$		-0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -3V, I_C = 0$		-0.1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE} = -1V, I_C = -50mA$	120	350	
		$V_{CE} = -1V, I_C = -500mA$	50		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$		-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500mA, I_B = -50mA$		-1.2	V
Transition frequency	$f_T$	$V_{CE} = -6V, I_C = -20mA$ $f = 30MHz$	150		MHz

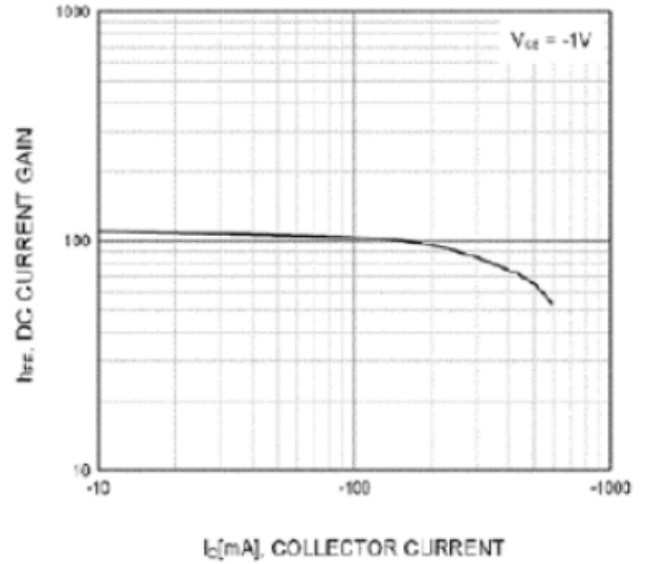
**CLASSIFICATION OF  $h_{FE(1)}$** 

Rank	L	H
Range	120-200	200-350

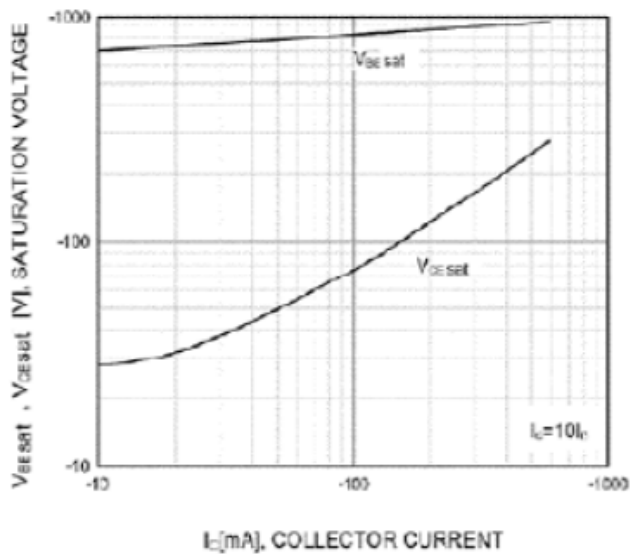
## TYPICAL CHARACTERISTICS



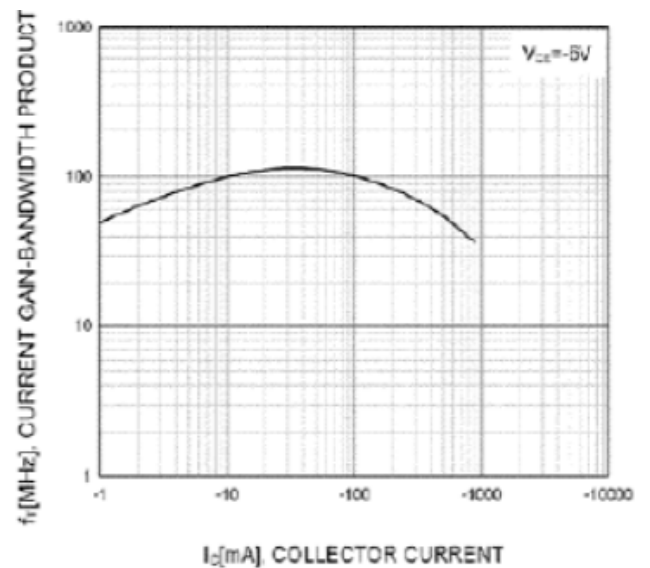
**Static Characteristic**



**DC current Gain**



**Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage**



**Current Gain Bandwidth Product**